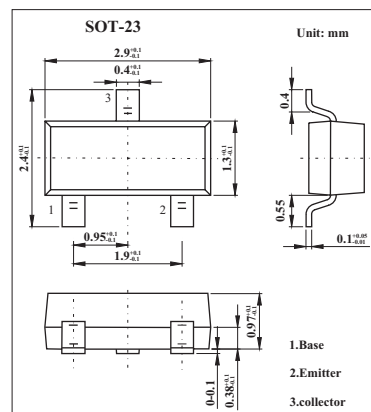


PNP Epitaxial Planar Silicon Transistors

2SB815

■ Features

- Ultrasmall package allows miniaturization in end products.
- Large current capacity ($I_c=0.7A$) and low-saturation voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-20	V
Collector-emitter voltage	V_{CE0}	-15	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_c	-0.7	A
Collector current (pulse)	I_{CP}	-1.5	A
Collector dissipation	P_c	200	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-55 to +125	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -15V, I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current Gain	h_{FE}	$V_{CE} = -2V, I_C = -50mA$	200		600	
Gain bandwidth product	f_T	$V_{CE} = -10V, I_C = -50mA$		250		MHz
Output capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		13		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5mA, I_B = -0.5mA$		-15	-35	mV
	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-60	-120	mV

■ h_{FE} Classification

Marking	B6	B7
h_{FE}	200~400	300~600